

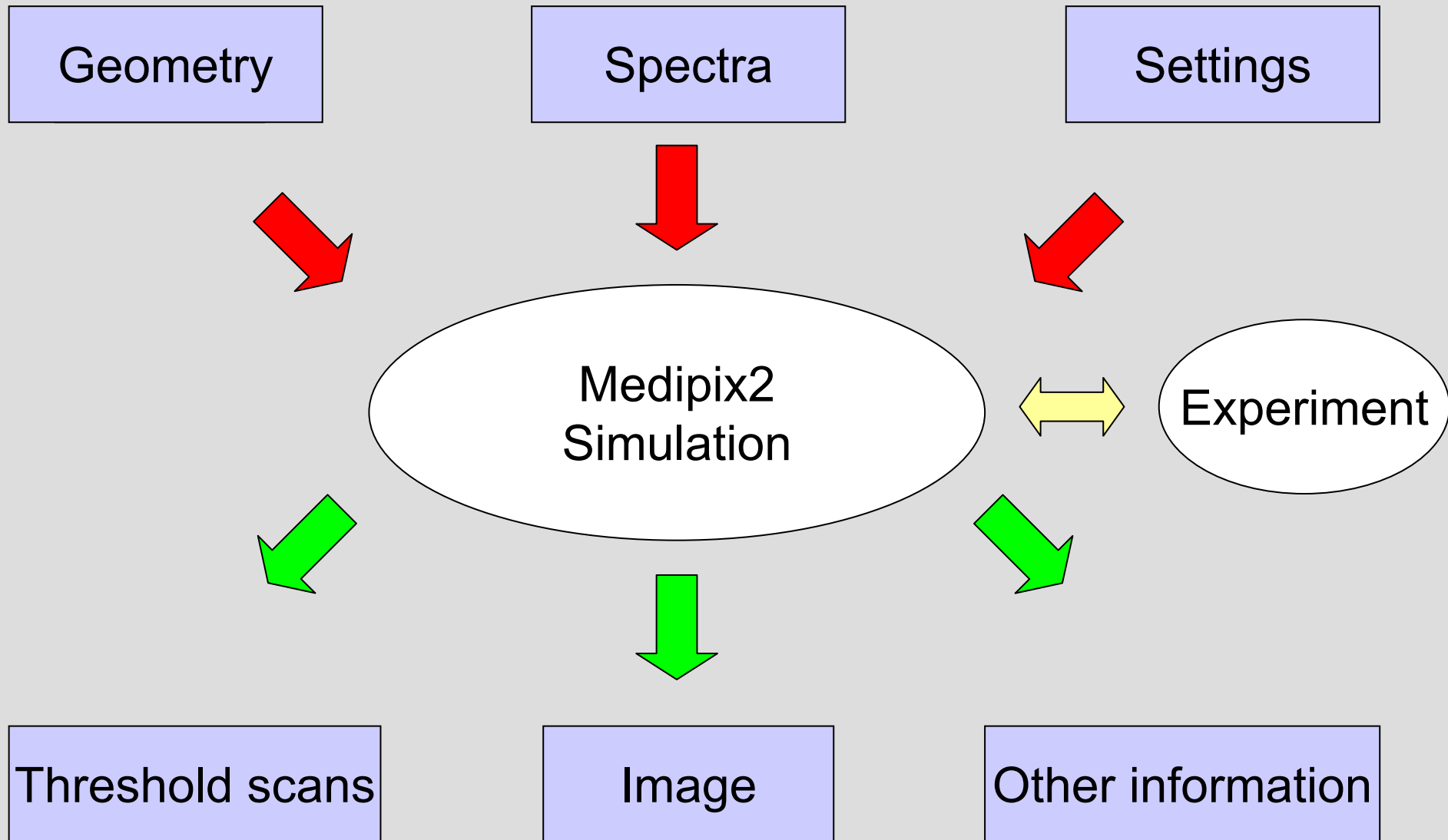
Investigation of Charge Carrier Transport and Charge Sharing in X-Ray Semiconductor Pixel Detectors such as Medipix2



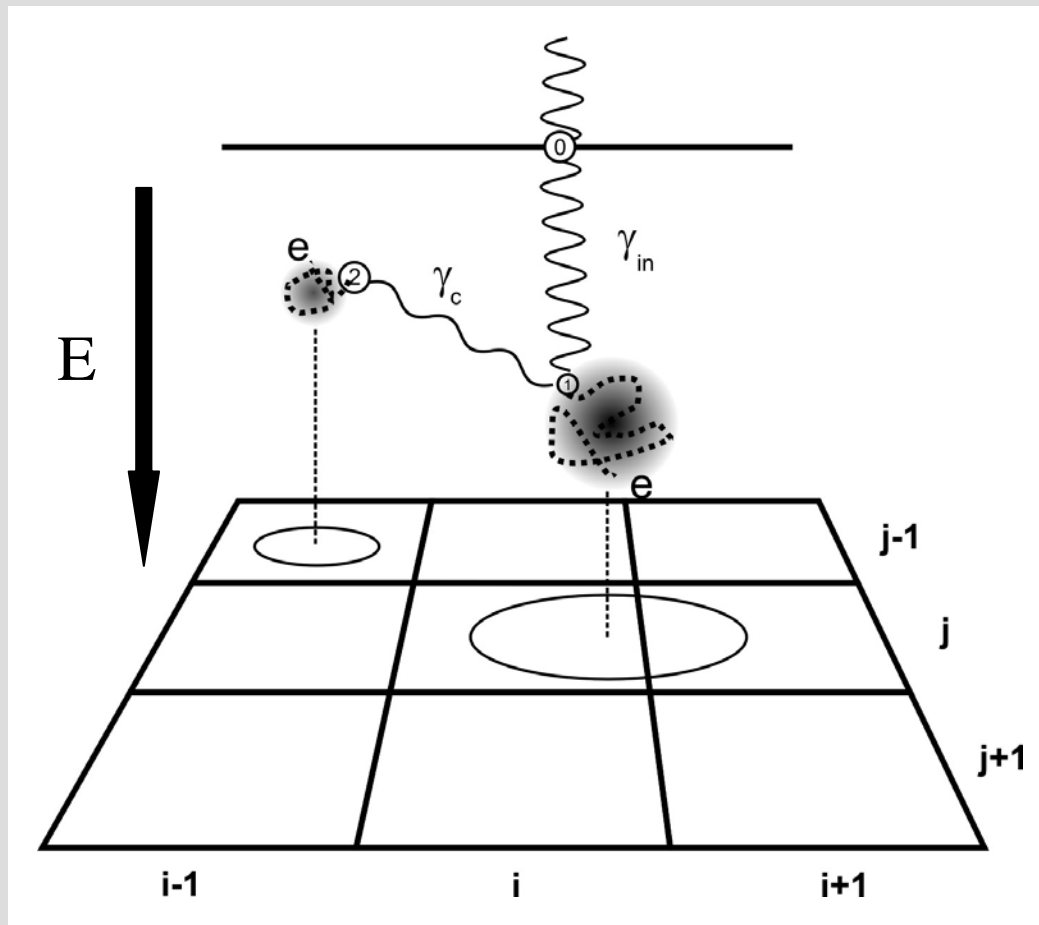
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09.07.06

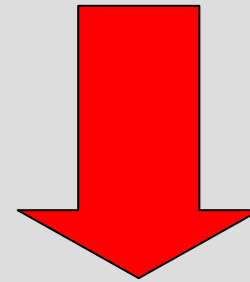
Motivation



Charge Sharing / Spreading



Diffusion

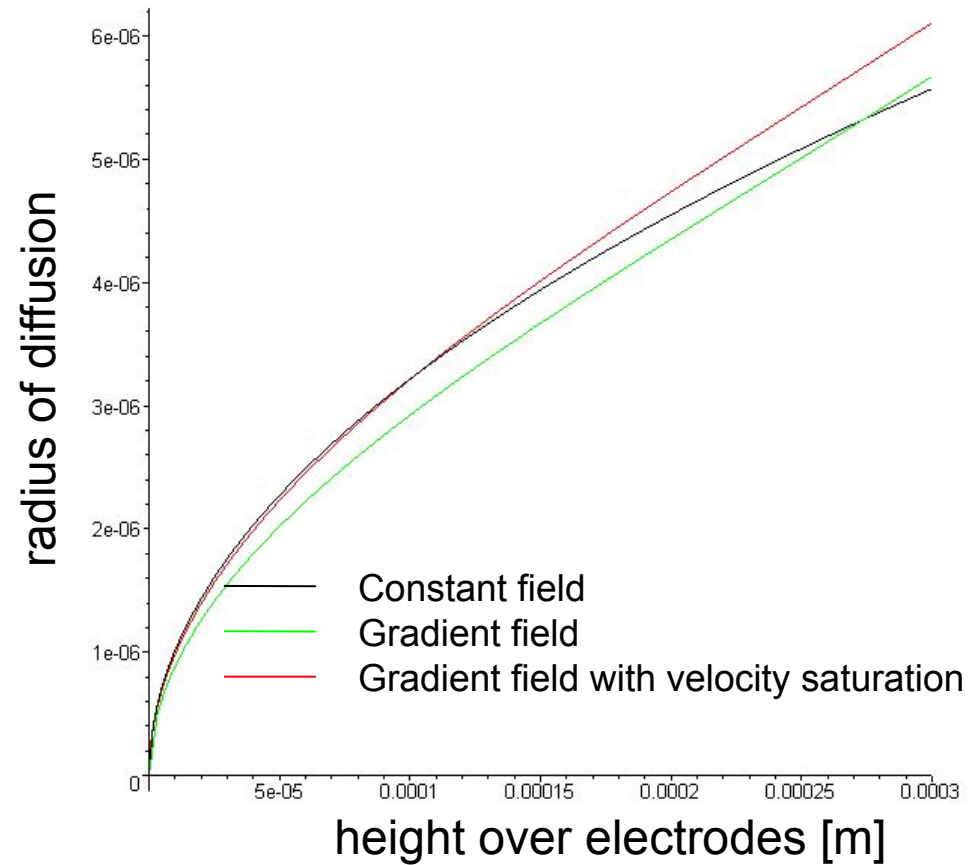
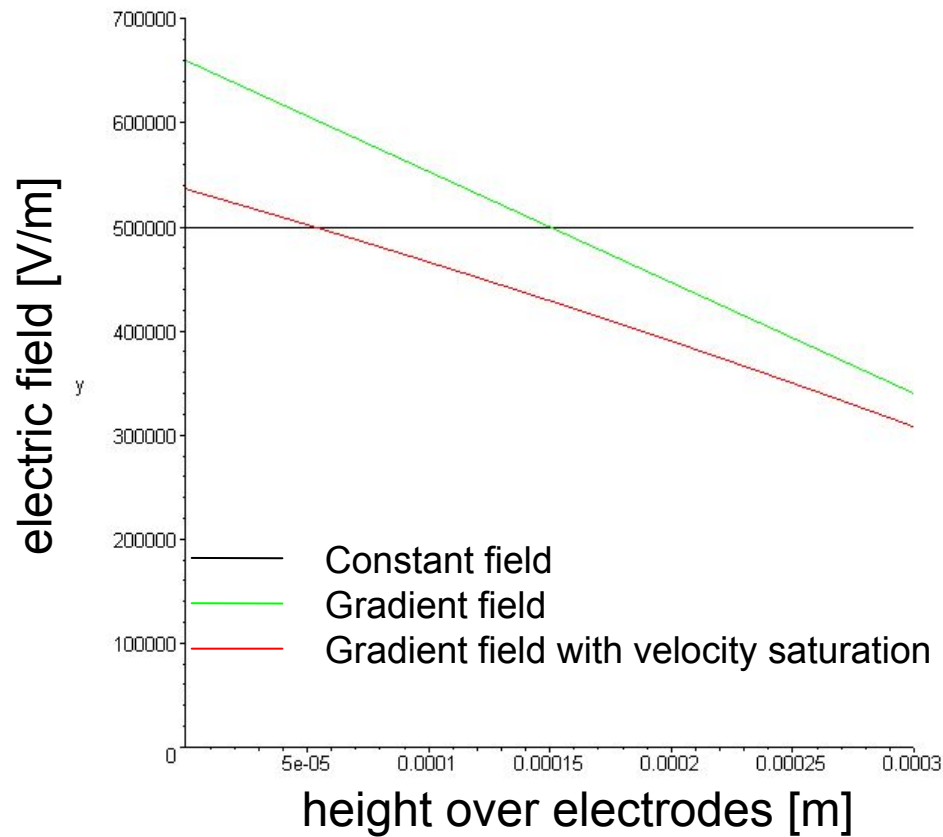


Spatial spreading

Energy distribution

Efficiency

Diffusion



$$\sigma^2 = 2Dt \text{ with } D = \frac{k_B T}{e} \mu \text{ and } t = \int_0^{z_0} dz \frac{1}{\mu(E)E(z)}$$

ROSI - Roentgen Simulation

Simulation of interaction

Gives location and energy deposition of interactions inside the sensor layer.



(x,y,z,E) of interaction

Simulation of diffusion

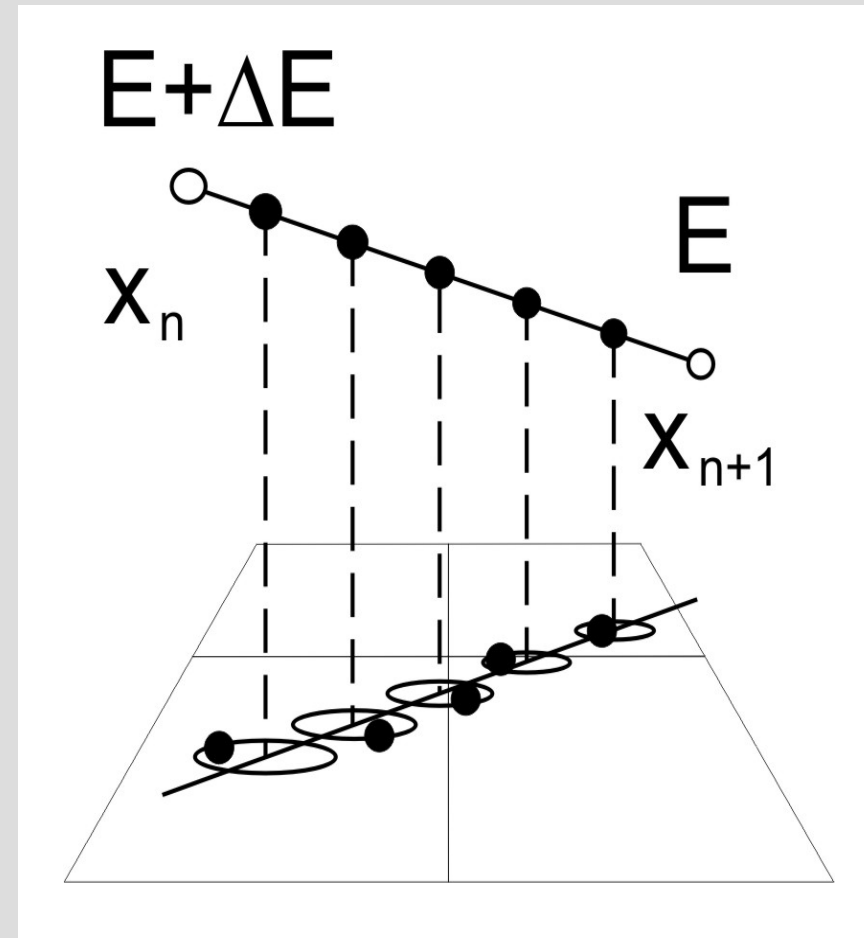
Each e-h pair is Gaussian distributed with $s = s(z)$ and projected in x,y plane.



(x,y) single charge 3.6 eV

Simulation of electronics

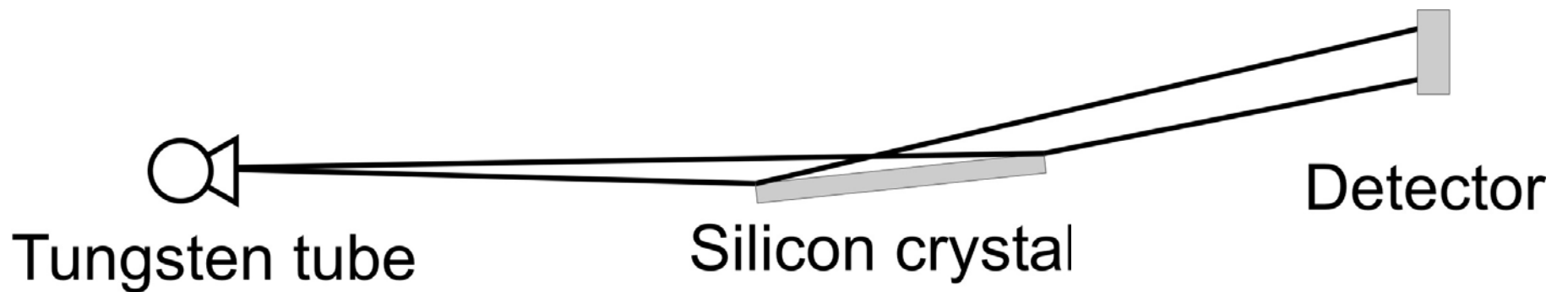
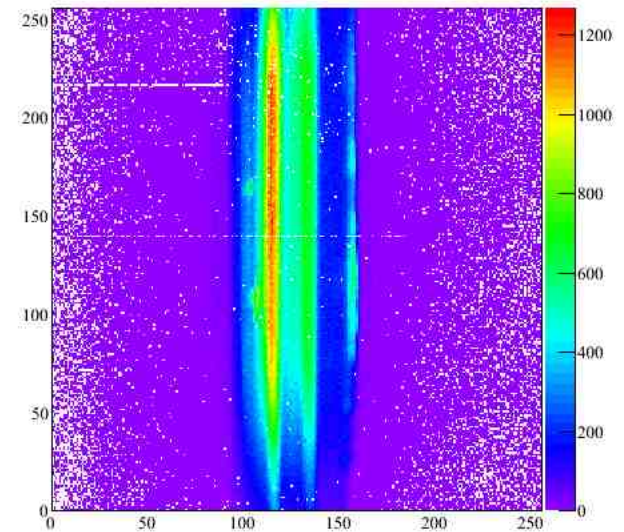
The energy in a spatial interval (Pixel) is also blurred Gaussian (electronic noise). The resulting energy per pixel is discriminated by the threshold and counted.



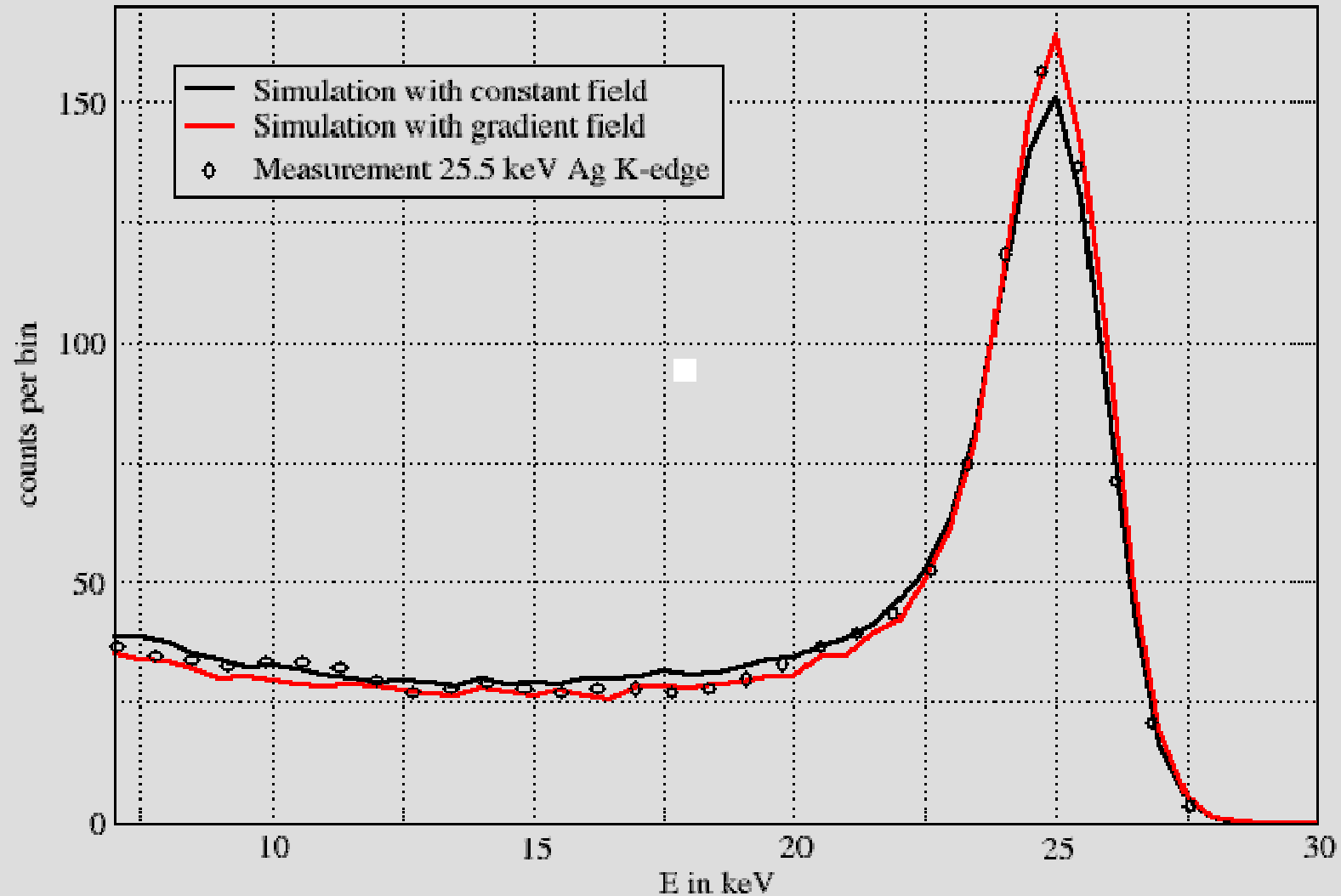
Experimental setup

- Bragg reflections as monoenergetic sources
- Threshold scans with Medipix2.

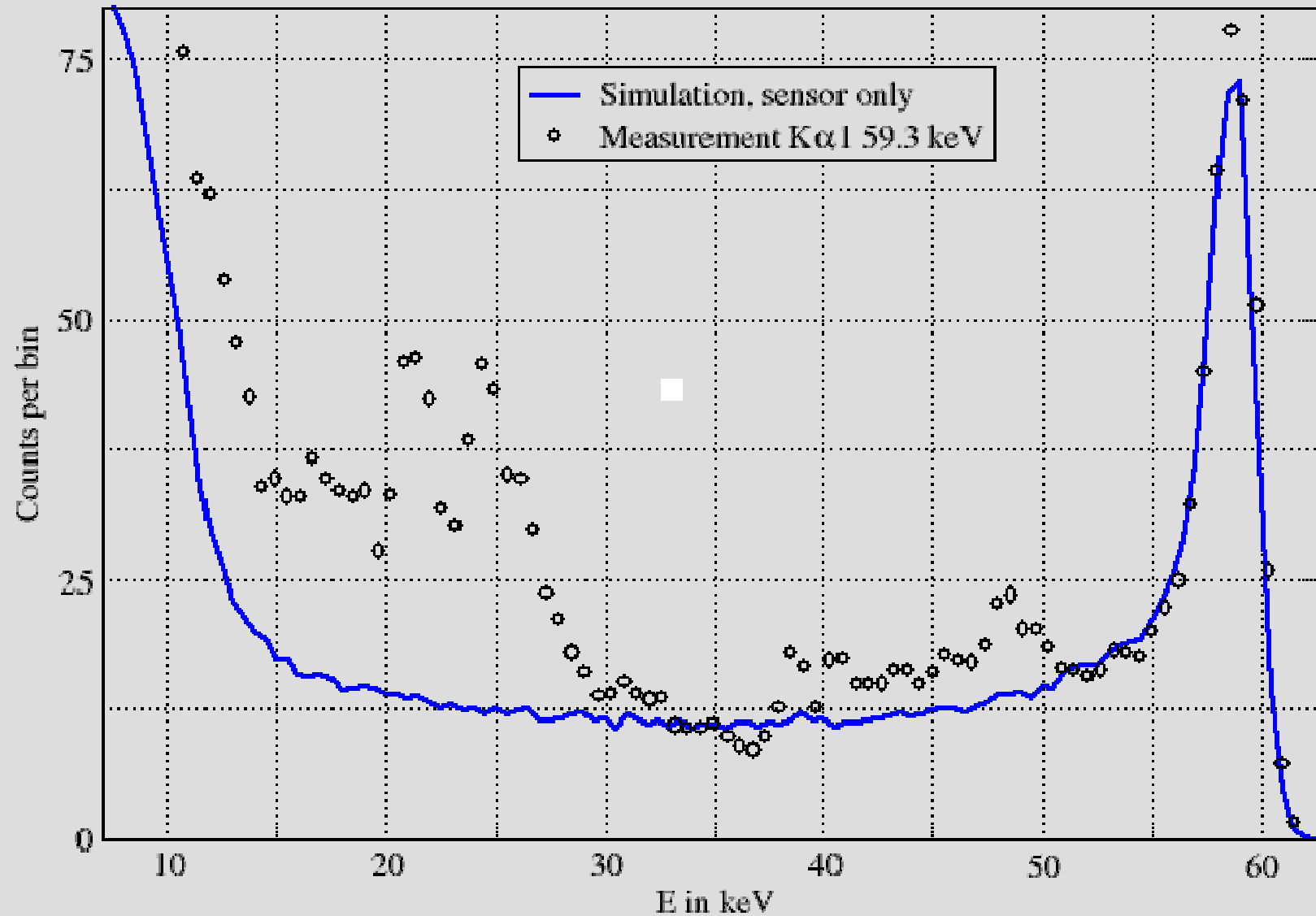
Tungston $K\alpha_1$ and $K\alpha_2$ line



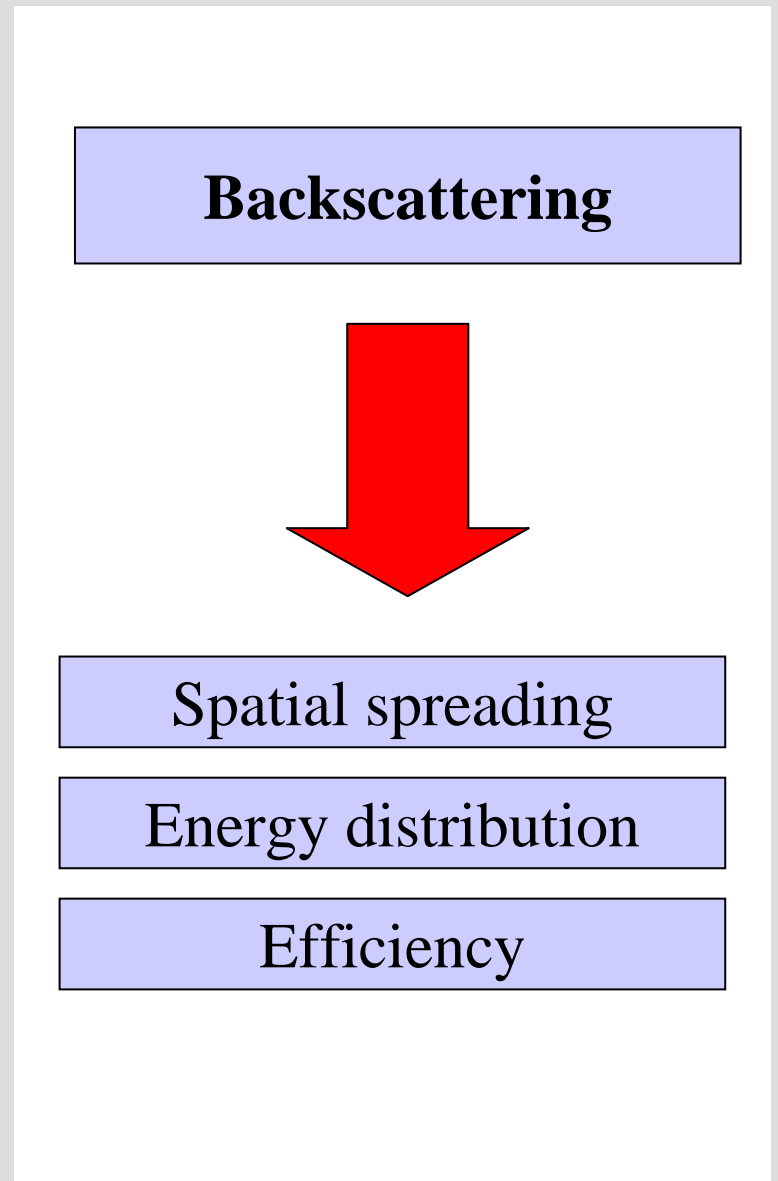
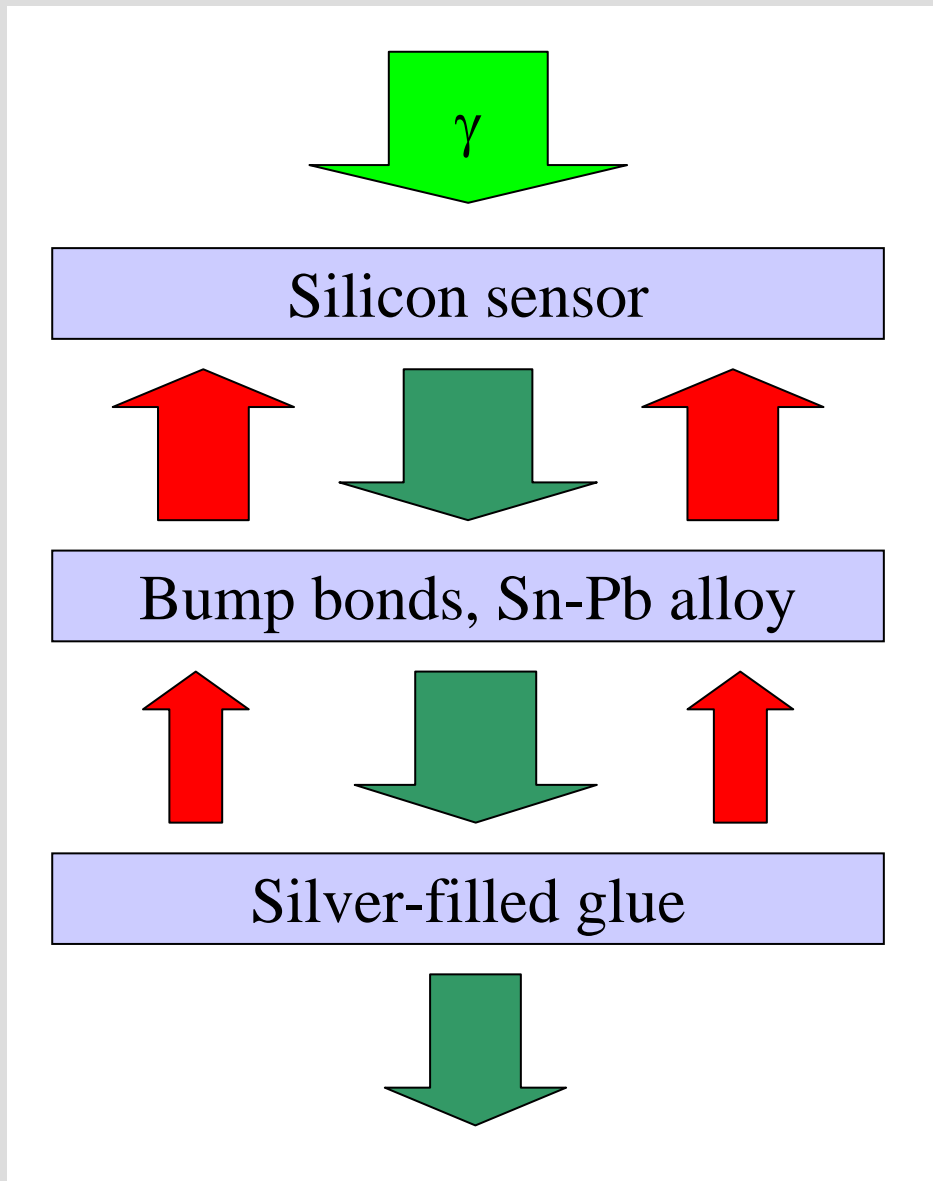
25.5 keV monoenergetic



59.3 keV monoenergetic

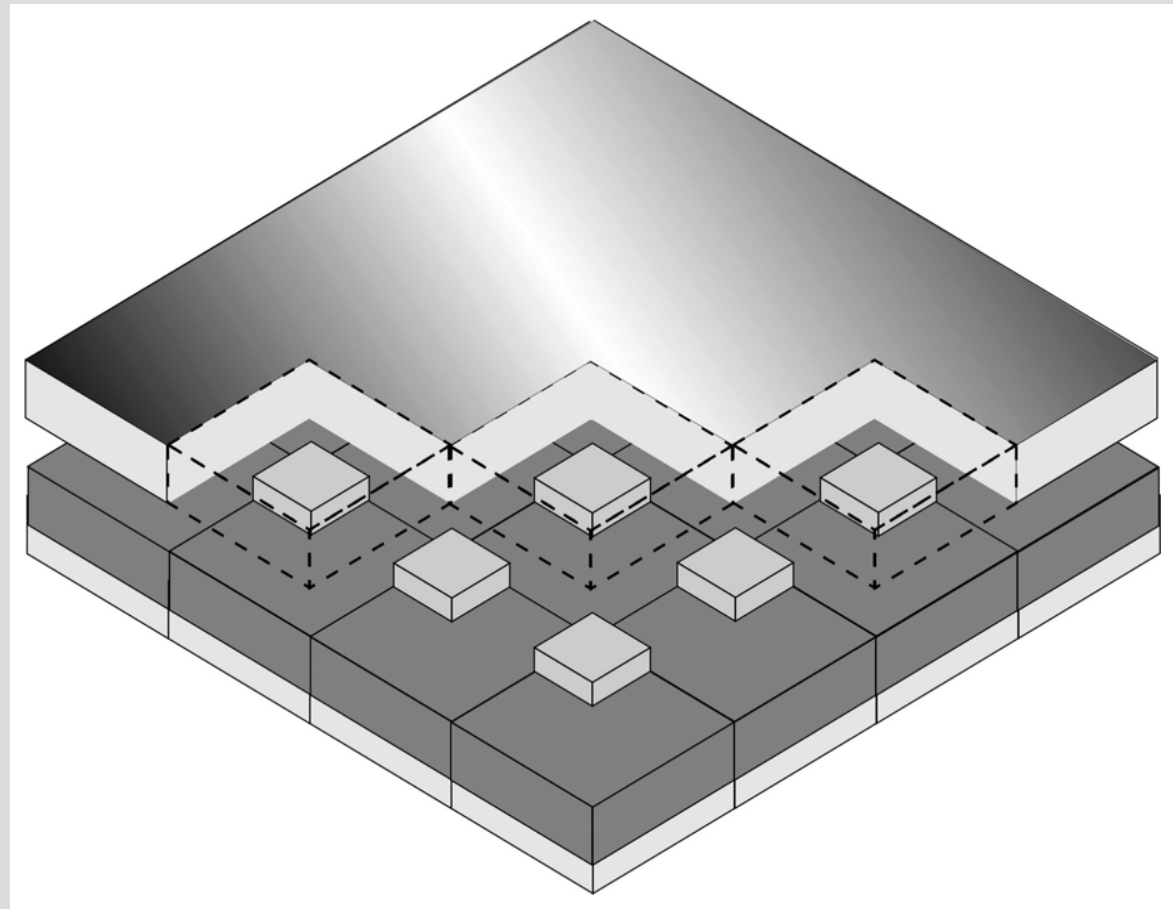


Backscattering



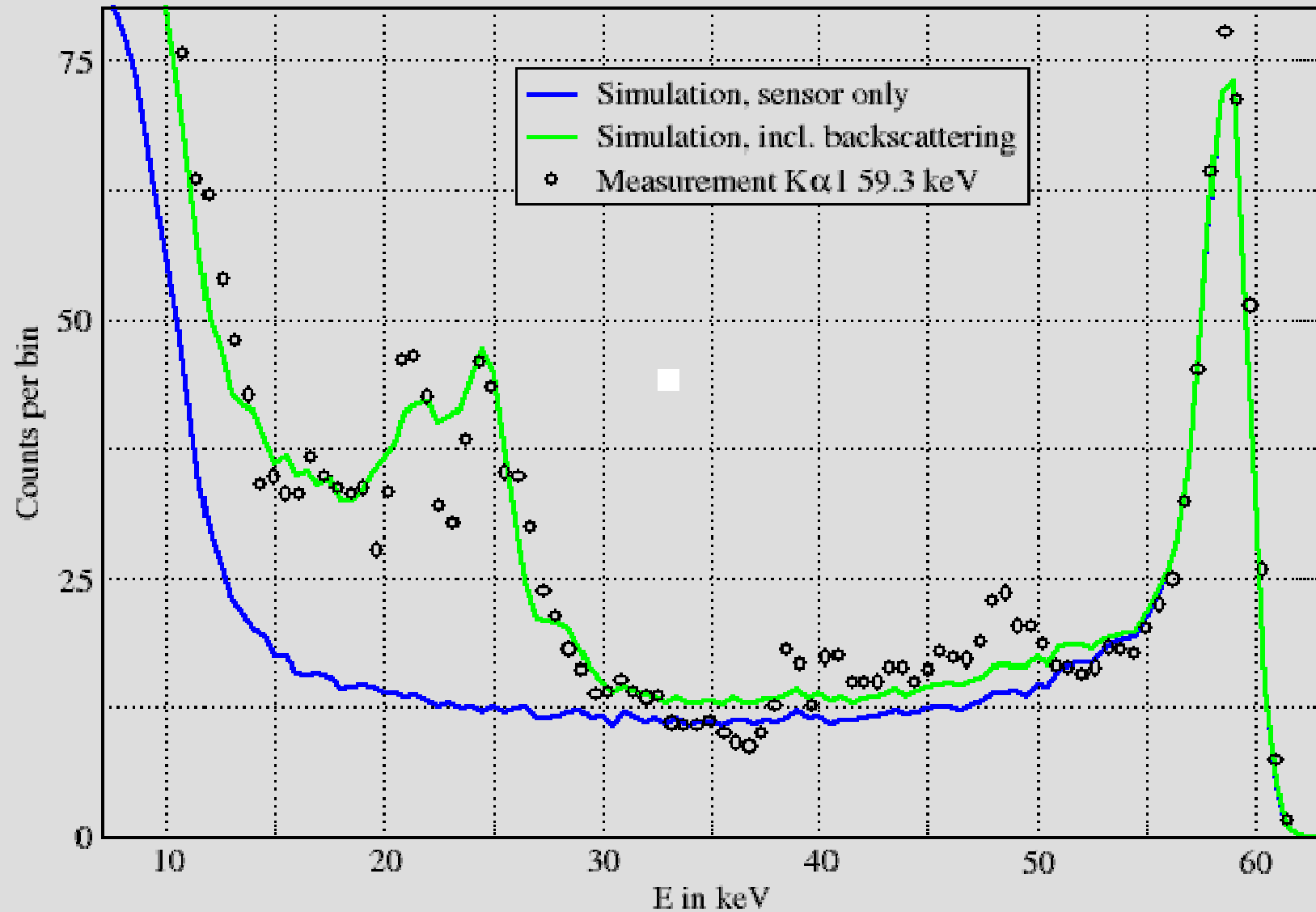
Implementation of the assembly

- Sensor, 700 μm silicon.
- Bump bonds, Sn/Pb alloy, cubics 25 μm .
- ASIC, 700 μm Si layer.
- Silver-filled glue 7 μm .



But: Simulation time up to a factor of 100.

59.3 keV



Conclusion

- For energies below 30 keV the energy response can be described by a convolution of a Gaussian charge distribution and the pixel aperture.
- For energies higher than 30 keV fluorescence of the assembly becomes significant (Silicon sensors) and the assembly as a whole has to be considered.

**Energy response of the Medipix2 detector
can be described by our simulation.**

Thank you, for your attention